Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- · Relay driver
- High-speed line driver
- · High-side loadswitch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	$V_{GS} = -10 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-5.3	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -4.2 A; T_j = 25 °C		-	35	45	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV35EPE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV35EPE	EK%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-5.3	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-4.2	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-2.7	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-17	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	480	mW
			[1]	-	1.2	W
		T _{sp} = 25 °C		-	6.95	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain d	iode			'	'	
I _S	source current	T _{amb} = 25 °C	[1]	-	-4	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

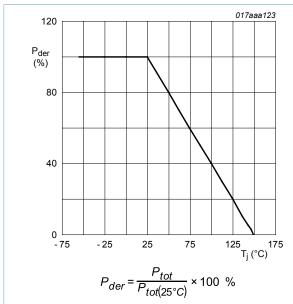


Fig. 1. Normalized total power dissipation as a function of junction temperature

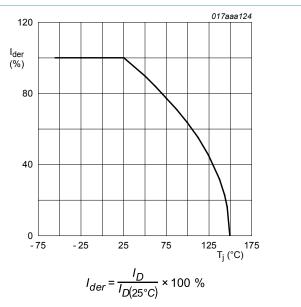
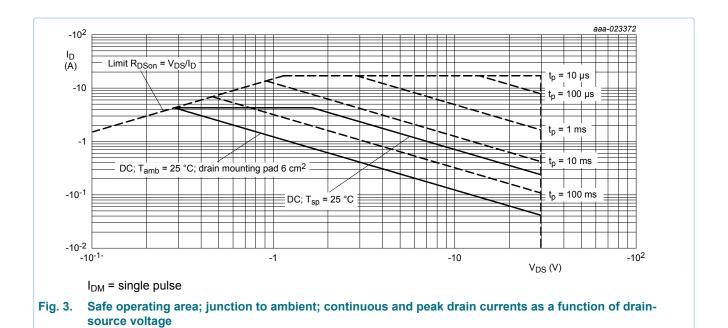


Fig. 2. Normalized continuous drain current as a function of junction temperature

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9. Thermal characteristics

Table 6. Thermal characteristics

and of the final determination							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	227	261	K/W
	from junction to ambient		[2]	-	91	104	K/W
	G	t ≤ 5 s	[2]	-	57	66	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	13	18	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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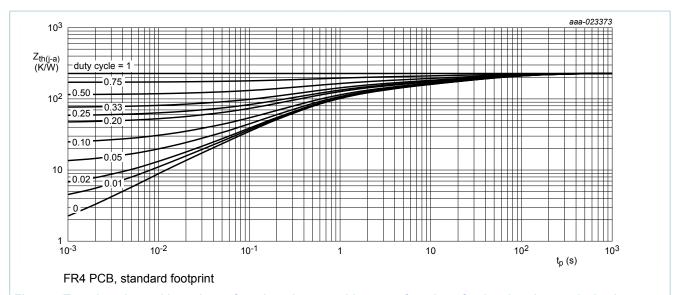


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

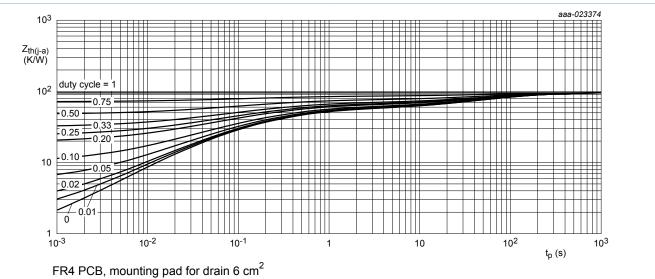


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
acteristics					
drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1	-2	-3	V
drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-1	μA
gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	10	μA
	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
	V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
drain-source on-state	V_{GS} = -10 V; I_D = -4.2 A; T_j = 25 °C	-	35	45	mΩ
resistance	V_{GS} = -10 V; I_D = -4.2 A; T_j = 150 °C	-	51	67	mΩ
	V_{GS} = -4.5 V; I_{D} = -3.3 A; T_{j} = 25 °C	-	49	72	mΩ
forward transconductance	V_{DS} = -10 V; I_{D} = -4.2 A; T_{j} = 25 °C	-	13.5	-	S
gate resistance	f = 1 MHz	-	13	-	Ω
naracteristics			•		
total gate charge	$V_{DS} = -15 \text{ V}; I_D = -4.2 \text{ A}; V_{GS} = -10 \text{ V};$	-	12.8	19.2	nC
gate-source charge	T _j = 25 °C	-	2.2	-	nC
gate-drain charge		-	2.2	-	nC
input capacitance	$V_{DS} = -15 \text{ V}$; f = 1 MHz; $V_{GS} = 0 \text{ V}$;	-	793	-	pF
output capacitance	I _j = 25 ℃	-	134	-	pF
reverse transfer capacitance		-	84	-	pF
turn-on delay time	$V_{DS} = -15 \text{ V}; I_D = -4.2 \text{ A}; V_{GS} = -10 \text{ V};$	-	6	-	ns
rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	19	-	ns
turn-off delay time		-	36	-	ns
fall time		-	19	-	ns
in diode		'	,		
source-drain voltage	$I_S = -4 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	_	-0.8	-1.2	V
	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance forward transconductance gate resistance gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time in diode	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current $V_{DS} = -30 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{DS} = -30 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = -4.2 \text{ A}; T_j = 25 \text{ °C}$ $V_{GS} = -10 \text{ V}; V_{DS} = -3.3 \text{ A}; T_j = 25 \text{ °C}$ $V_{DS} = -4.5 \text{ V}; I_D = -4.2 \text{ A}; T_j = 25 \text{ °C}$ $V_{DS} = -10 \text{ V}; I_D = -4.2 \text{ A}; T_j = 25 \text{ °C}$ $V_{DS} = -10 \text{ V}; I_D = -4.2 \text{ A}; T_j = 25 \text{ °C}$ $V_{DS} = -10 \text{ V}; I_D = -4.2 \text{ A}; V_{GS} = -10 \text{ V}; I_D = -4.2 \text{ A}; I_$	acteristics drain-source breakdown voltage $I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$ -30 gate-source threshold voltage $I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 ^{\circ}C$ -1 drain leakage current voltage $V_{DS} = -30 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ - gate leakage current voltage $V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ - $V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ - $V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ - $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ - $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ - $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ - $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ - $V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 ^{\circ}C$ - forward transconductance $V_{DS} = -10 V; V_{DS} = -4.2 A; T_j = 25 ^{\circ}C$ - forward transconductance $V_{DS} = -10 V; V_{DS} = -4.2 A; V_{GS} = -10 V;$ - gate resistance $f = 1 MHz$ - naracteristics total gate charge $V_{DS} = -15 V; V_{DS} = -4.2 A; V_{GS} = -10 $	drain-source breakdown voltage I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C -30	

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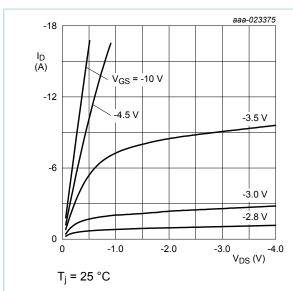


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

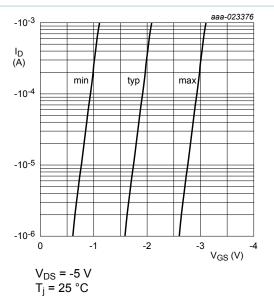


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

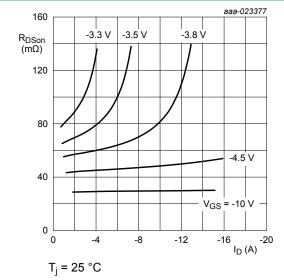


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

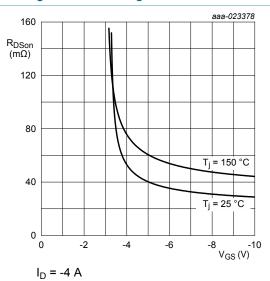


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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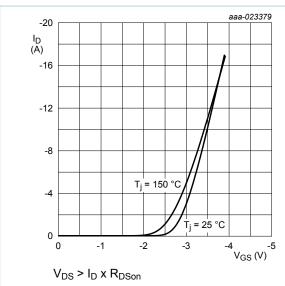


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

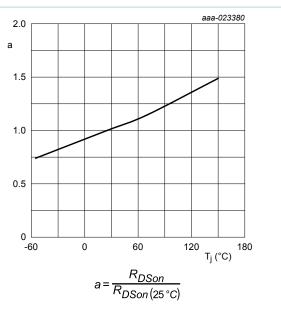


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

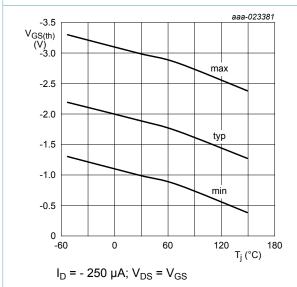


Fig. 12. Gate-source threshold voltage as a function of junction temperature

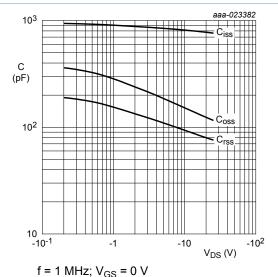
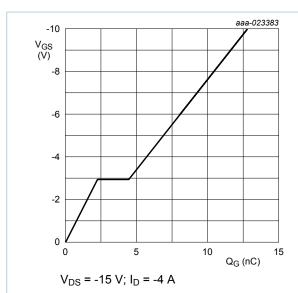


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1}
Q_{GS2}
Q_{GG(tot)}
003aaa508

Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

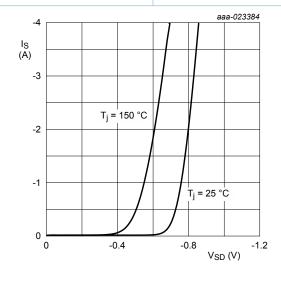
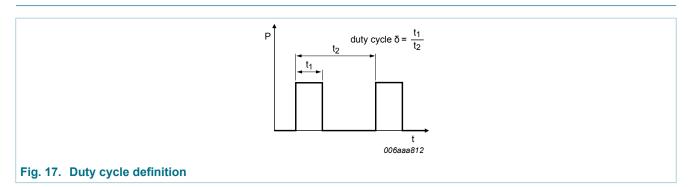


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

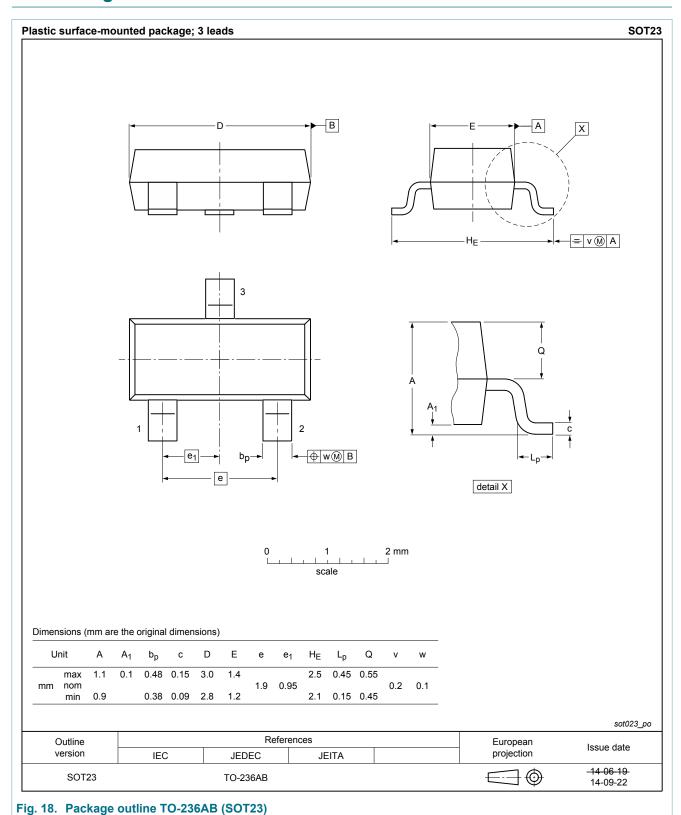
 $V_{GS} = 0 V$



PMV35EPE

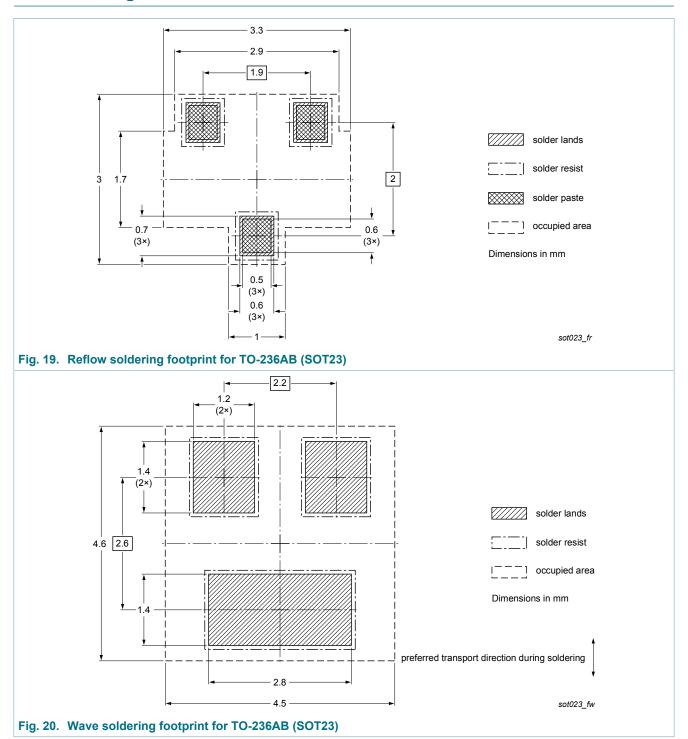
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV35EPE v.1	20160706	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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